



# 《风光欣》技术资料

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## 2SD2098

NPN EPITAXIAL SILICON TRANSISTOR

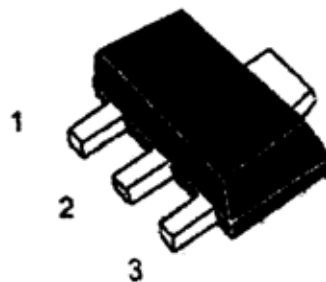
### ●Features

1) LOW  $V_{CE(sat)}$ .

$$V_{CE(sat)} = 0.25V \text{ (Typ.)}$$

$$(I_c/I_B = 4A / 0.1A)$$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Emitter -Base Voltage	$V_{EBO}$	6	V
Collector Current (DC)	$I_c$	5	A
Collector Current (Pulse)	$I_c$	10	A
Collector Dissipation ( $T_c=25$ )	$P_c$	500	mW
Collector Dissipation ( $T_a=25$ )	$P_c$	2	W
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~150	



1,Base 2,Collector 3,Emitter

### ELECTRICAL CHARACTERISTICS( $T_a=25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cutoff Current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$			0.5	$\mu A$
Emitter-Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_c = 0$			0.5	$\mu A$
*DC Current Gain	$h_{FE}$	$V_{CE} = 2V, I_c = 0.5A$	120		390	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = 4A, I_B = 0.1A$		0.25	1	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 6V, I_E = -50mA$		150		MHZ
Output Capacitance	$C_{OB}$	$V_{CB} = 20V, f = 1MHZ$		30		pF

### HFE CLASSIFICATION

Classification	Q	R
HFE	120-270	180-390